N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 800V
- I_D
- $R_{DS(ON)}$(at V_{GS}=10V) 1.2
- 100% EAS Tested
- 100% V_{DS}

v **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter

■ Typical Electrical and Thermal Characteristics Diagrams

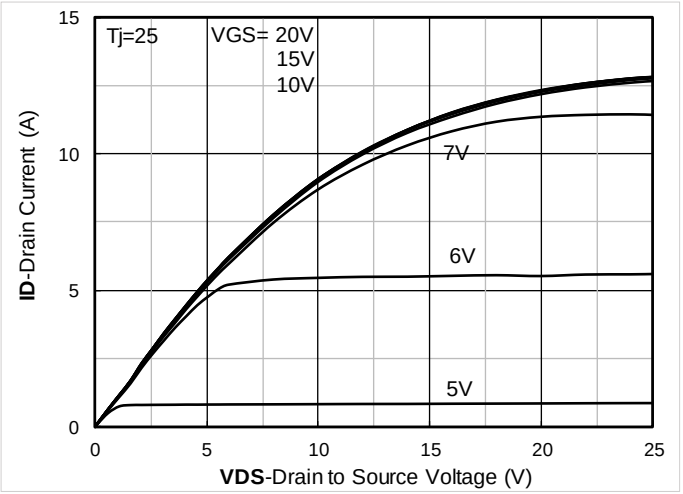

Figure 1. Output Characteristics

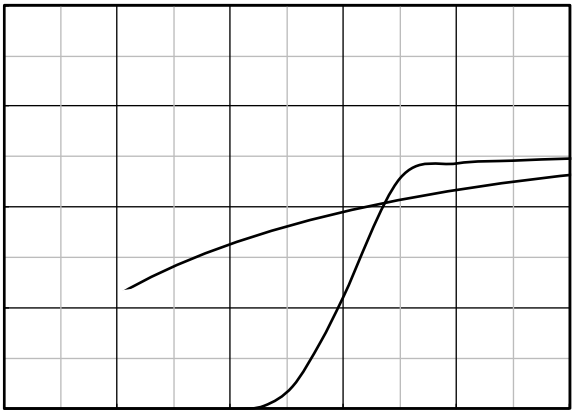

Figure 2.

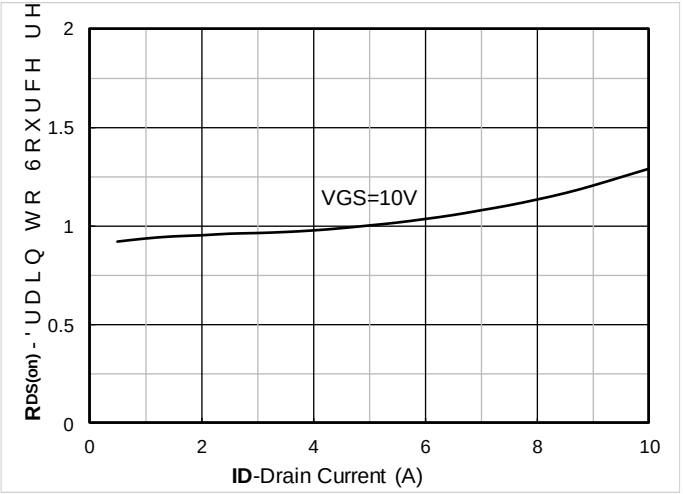

Figure 7. $R_{DS(on)}$ VS Drain Current

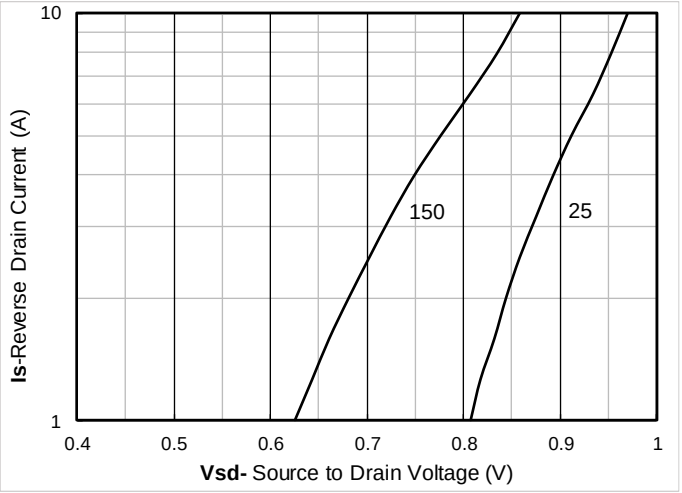

Figure 8. Forward characteristics of reverse diode

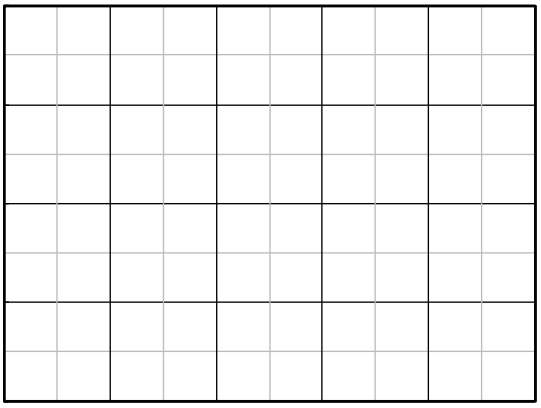

Figure 9. Normalized breakdown voltage

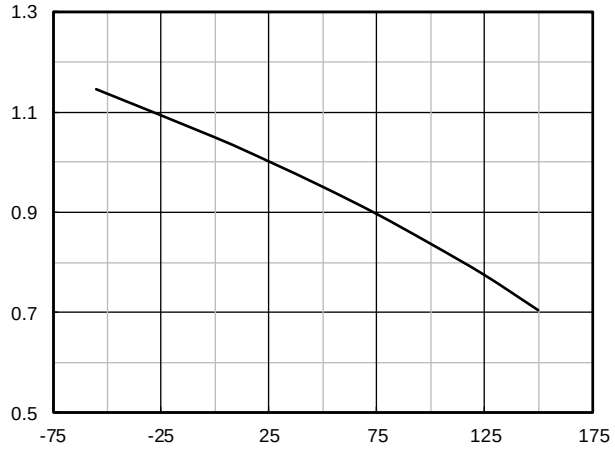

Figure 10. Normalized Threshold voltage

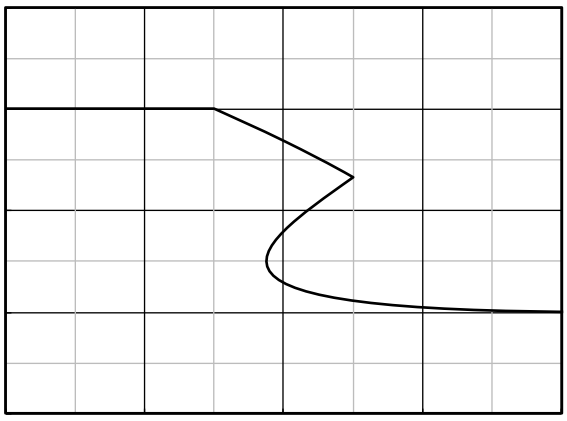

Figure 11. Current dissipation

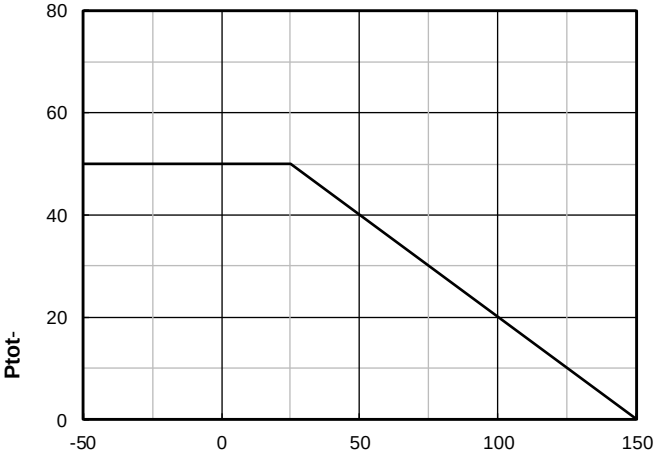

Figure 12. Power dissipation

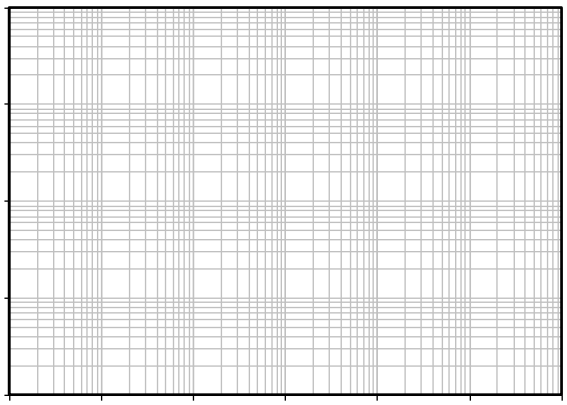

Figure 13. Maximum Transient Thermal Impedance

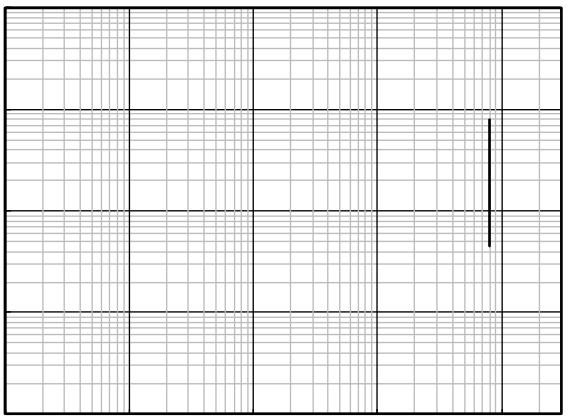

Figure 14. Safe Operation Area

v Test Circuits & Waveforms

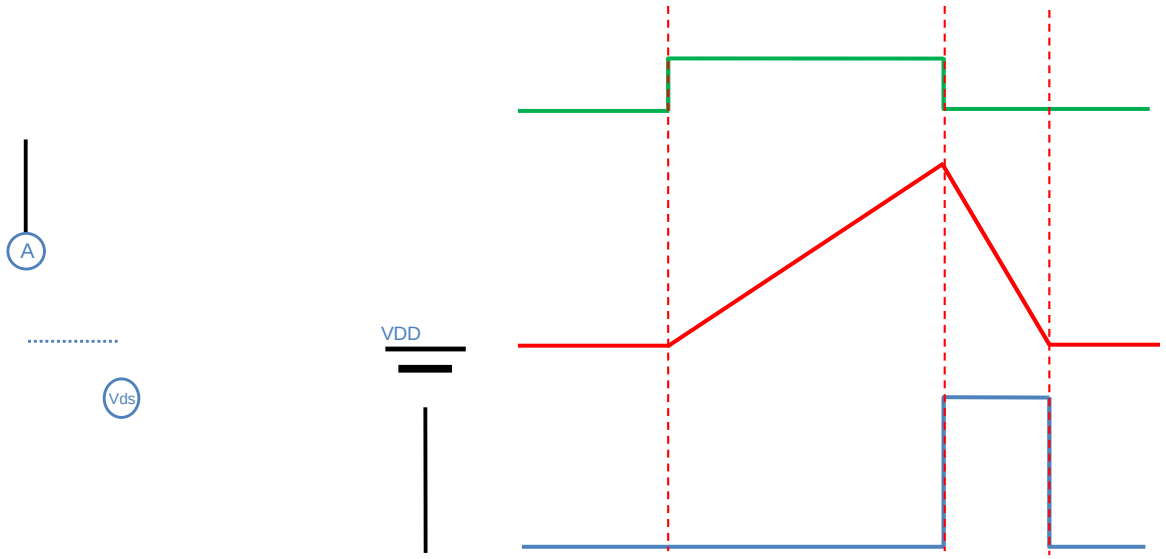

Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

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